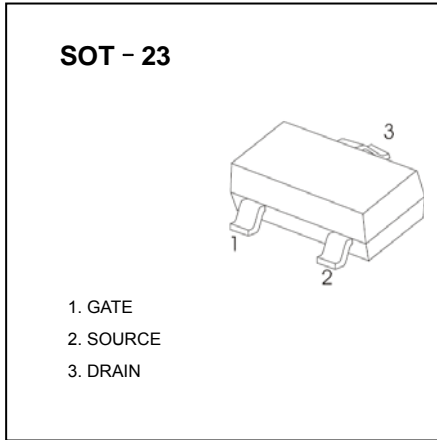
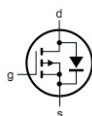
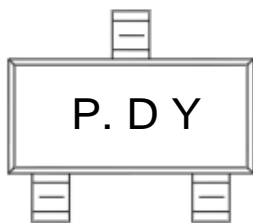


P-Channel Enhancement Mode MOSFET

■ Features

- $V_{DS} (V) = -50V$
- $I_D = -0.13 A$
- $R_{DS(ON)} \leq 10 \Omega$ ($V_{GS} = -5V$)

MARKING



SOT - 23

- 1. GATE
- 2. SOURCE
- 3. DRAIN

■ Absolute Maximum Ratings $T_a = 25^\circ C$ unless otherwise specified

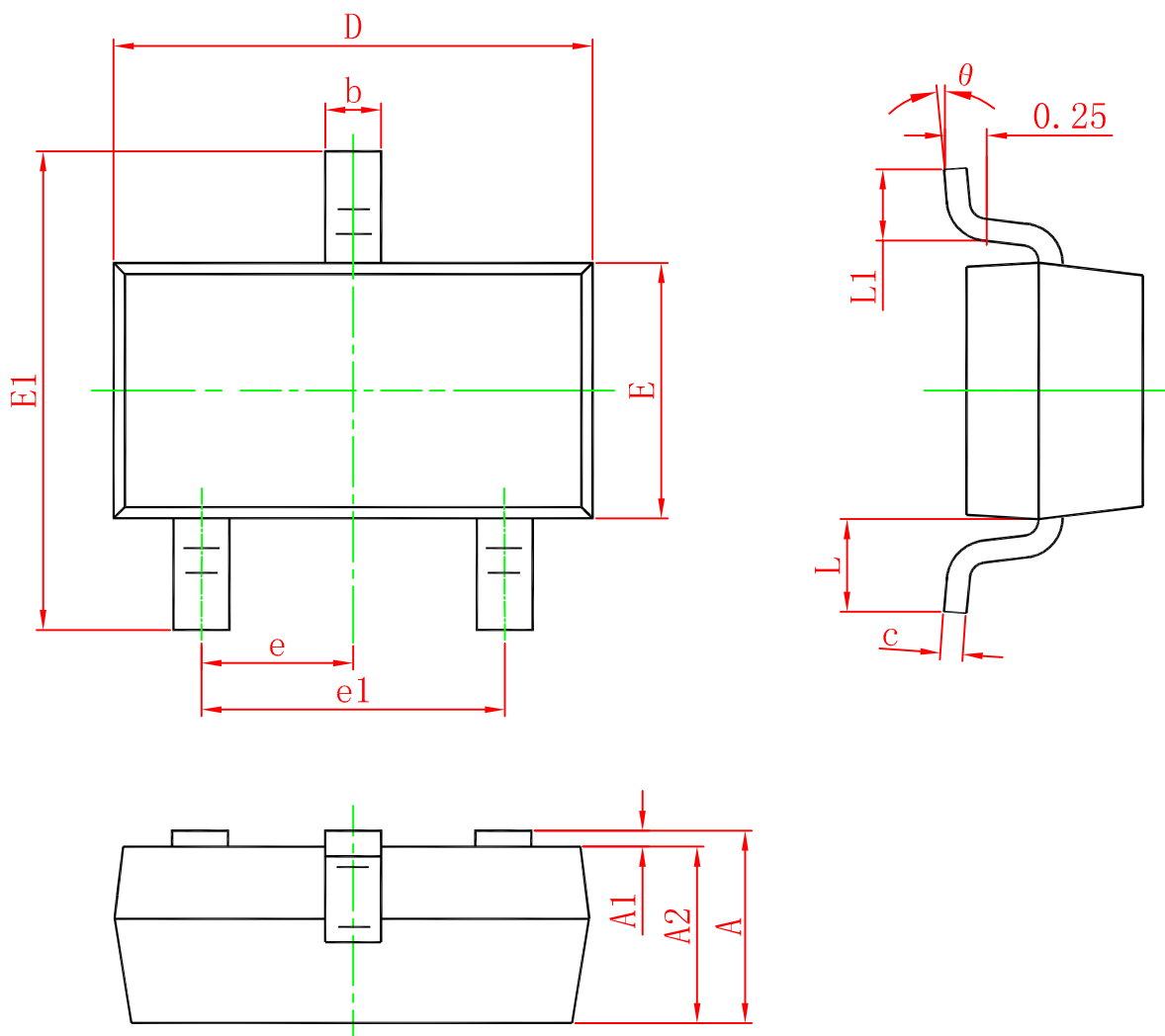
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current *	I_D	- Continuous	-130
		- Pulsed	-520
Total Power Dissipation *	P_d	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ C/W$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ C$

* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch;

■ Electrical Characteristics $T_a = 25^\circ C$ unless otherwise specified

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	B_{VDSS}	$V_{GS} = 0V, I_D = -250\mu A$	-50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -50V, V_{GS} = 0V, T_J = 25^\circ C$			-15	μA
		$V_{DS} = -50V, V_{GS} = 0V, T_J = 125^\circ C$			-60	μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -1mA$	-0.8		-2.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -5V, I_D = -100mA$			10	Ω
Forward Transconductance	g_{FS}	$V_{DS} = -25V, I_D = -0.1A$	0.05			S
Input Capacitance	C_{iss}	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$			45	pF
Output Capacitance	C_{oss}				25	pF
Reverse Transfer Capacitance	C_{rss}				12	pF
Turn-On Delay Time	$t_{d(ON)}$	$V_{DD} = -30V, I_D = -0.27A,$		10		ns
Turn-Off Delay Time	$t_{d(OFF)}$	$R_{GEN} = 50\Omega, V_{GS} = -10V$		18		ns

P-Channel Enhancement Mode MOSFET
SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Youtai](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [FCA20N60_F109](#) [FDZ595PZ](#) [AOD464](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#)
[405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#) [PSMN4R2-30MLD](#)
[TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#)
[NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-](#)
[7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [STU5N65M6](#) [C3M0021120D](#) [DMN13M9UCA6-7](#)
[BSS340NWH6327XTSA1](#) [MCM3400A-TP](#) [DMTH10H4M6SPS-13](#) [IRF40SC240ARMA1](#) [IPS60R1K0PFD7SAKMA1](#)
[IPS60R360PFD7SAKMA1](#) [IPS60R600PFD7SAKMA1](#)